

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

**TC74HC4051AP, TC74HC4051AF, TC74HC4051AFT
 TC74HC4052AP, TC74HC4052AF, TC74HC4052AFT
 TC74HC4053AP, TC74HC4053AF, TC74HC4053AFT**

TC74HC4051AP/AF/AFT

8-Channel Analog
 Multiplexer/Demultiplexer

TC74HC4052AP/AF/AFT

Dual 4-Channel Analog
 Multiplexer/Demultiplexer

TC74HC4053AP/AF/AFT

Triple 2-Channel Analog
 Multiplexer/Demultiplexer

The TC74HC4051A/4052A/4053A are high speed CMOS ANALOG MULTIPLEXER/DEMULITPLEXER fabricated with silicon gate C²MOS technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The TC74HC4051A has an 8 channel configuration, the TC74HC4052A has a 4 channel × 2 configuration and the TC74HC4053A has a 2 channel × 3 configuration.

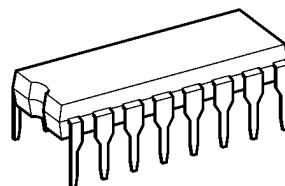
The digital signal to the control terminal turns “ON” the corresponding switch of each channel a large amplitude signal (VCC – VEE) can then be switched by the small logical amplitude (VCC – GND) control signal.

For example, in the case of VCC = 5 V, GND = 0 V, VEE = -5 V, signals between -5 V and +5 V can be switched from the logical circuit with a single power supply of 5 V. As the ON-resistance of each switch is low, they can be connected to circuits with low input impedance.

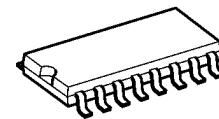
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

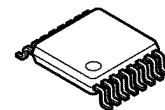
- High speed: t_{pd} = 15 ns (typ.) at VCC = 5 V, VEE = 0 V
- Low power dissipation: I_{CC} = 4 μA (max) at Ta = 25°C
- High noise immunity: V_{NH} = V_{NIL} = 28% VCC (min)
- Low ON resistance: R_{ON} = 50 Ω (typ.) at VCC – VEE = 9 V
- High noise immunity: THD = 0.02% (typ.) at VCC – VEE = 9 V
- Pin and function compatible with 4051/4052/4053B

TC74HC4051AP, TC74HC4052AP,
 TC74HC4053AP

DIP16-P-300-2.54A

TC74HC4051AF, TC74HC4052AF,
 TC74HC4053AF

SOP16-P-300-1.27A

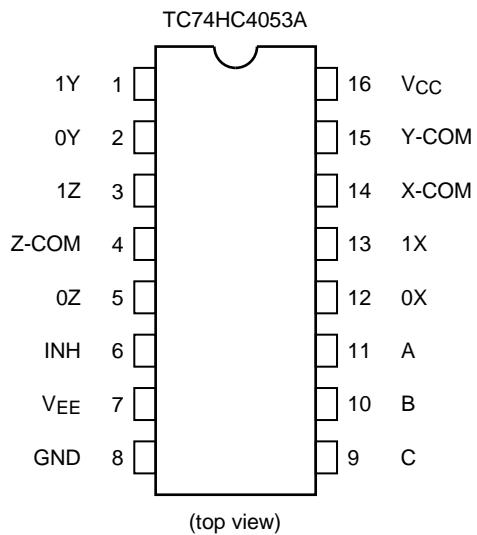
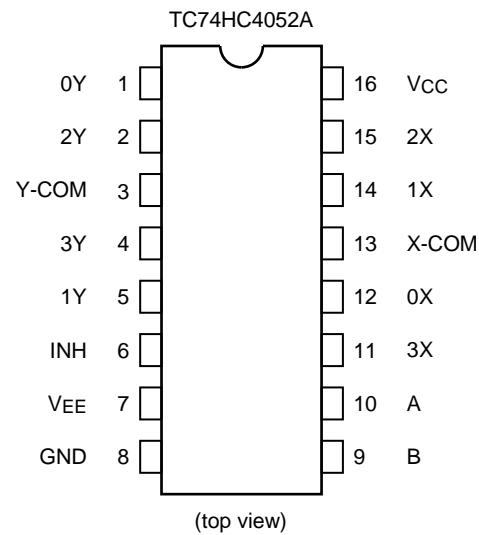
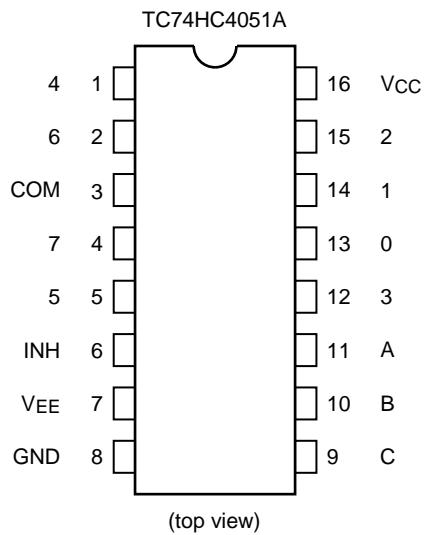
TC74HC4051AFT, TC74HC4052AFT,
 TC74HC4053AFT

TSSOP16-P-0044-0.65A

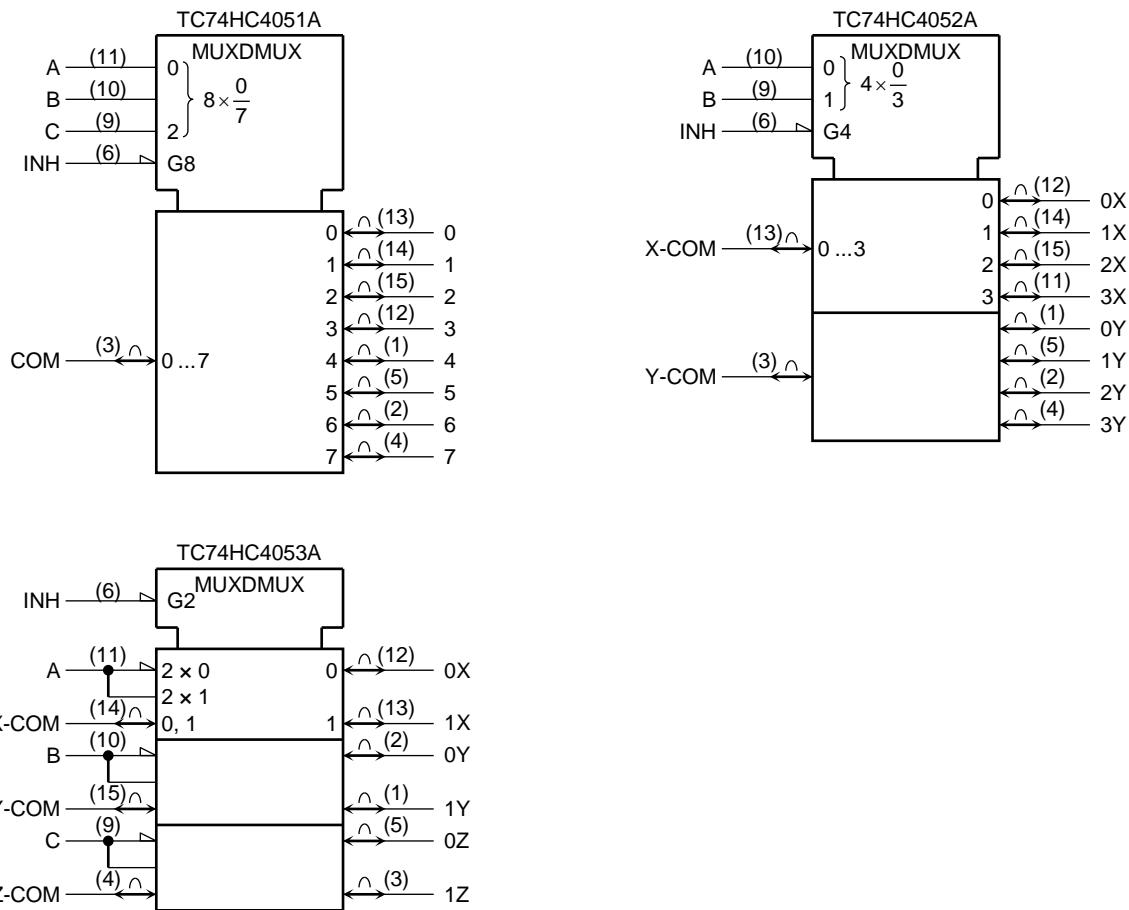
Weight

DIP16-P-300-2.54A	: 1.00 g (typ.)
SOP16-P-300-1.27A	: 0.18 g (typ.)
TSSOP16-P-0044-0.65A	: 0.06 g (typ.)

Start of commercial production
 1986-05

Pin Assignment

IEC Logic Symbol

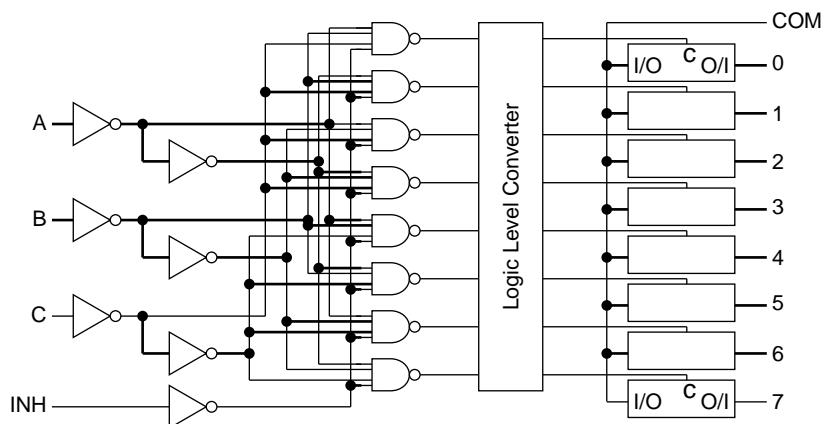
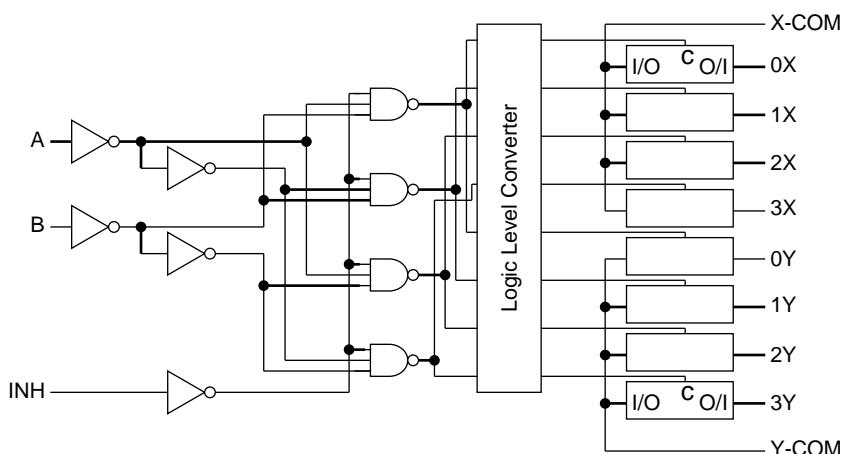
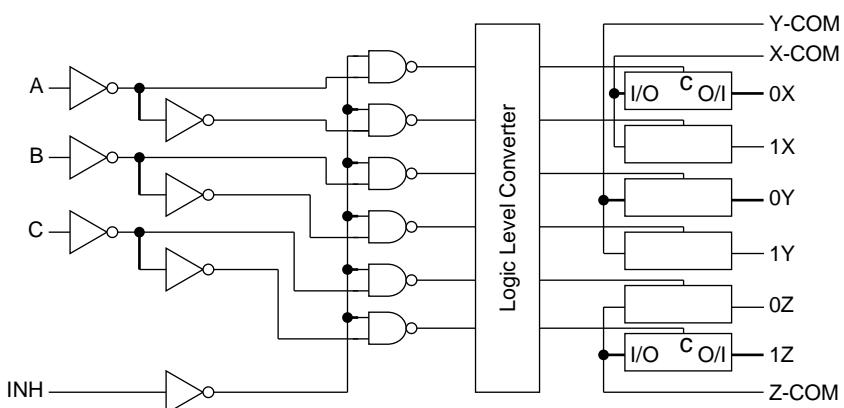


Truth Table

Control Inputs				“ON” Channel		
Inhibit	C*	B	A	HC4051A	HC4052A	HC4053A
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z
L	L	L	H	1	1X, 1Y	1X, 0Y, 0Z
L	L	H	L	2	2X, 2Y	0X, 1Y, 0Z
L	L	H	H	3	3X, 3Y	1X, 1Y, 0Z
L	H	L	L	4	—	0X, 0Y, 1Z
L	H	L	H	5	—	1X, 0Y, 1Z
L	H	H	L	6	—	0X, 1Y, 1Z
L	H	H	H	7	—	1X, 1Y, 1Z
H	X	X	X	None	None	None

X: Don't care

*: Except HC4052A

System Diagram**TC74HC4051A****TC74HC4052A****TC74HC4053A**

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7	V
Supply voltage range	V _{CC} -V _{EE}	-0.5 to 13	V
Control input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
Switch I/O voltage	V _{I/O}	V _{EE} - 0.5 to V _{CC} + 0.5	V
Control input diode current	I _{CCK}	±20	mA
I/O diode current	I _{IOK}	±20	mA
Switch through current	I _T	±25	mA
DC V _{CC} or ground current	I _{CC}	±50	mA
Power dissipation	P _D	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T _{STG}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	2 to 6	V
Supply voltage range	V _{EE}	-6 to 0	V
Supply voltage range	V _{CC} -V _{EE}	2 to 12	V
Control input voltage	V _{IN}	0 to V _{CC}	V
Switch I/O voltage	V _{I/O}	V _{EE} to V _{CC}	V
Operating temperature	T _{OPR}	-40 to 85	°C
Control input rise and fall time	t _r , t _f	0 to 1000 (V _{CC} = 2.0 V) 0 to 500 (V _{CC} = 4.5 V) 0 to 400 (V _{CC} = 6.0 V)	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused control inputs must be tied to either V_{CC} or GND.

Electrical Characteristics**DC Characteristics**

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
		VEE (V)	VCC (V)	Min	Typ.	Max	Min	Max		
High-level control input voltage	VIHC	—	2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low-level control input voltage	VILC	—	2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
ON resistance	RON	VIN = VIHC or VIIC	GND	4.5	—	85	180	—	225	Ω
		Vi/O = VCC to VEE	-4.5	4.5	—	55	120	—	150	
		Ii/O ≤ 2 mA	-6.0	6.0	—	50	100	—	125	
		VIN = VILC or VIIC	GND	2.0	—	150	—	—	—	
		Vi/O = VCC or VEE	GND	4.5	—	70	150	—	190	
		Ii/O ≤ 2 mA	-4.5	4.5	—	50	100	—	125	
		—	-6.0	6.0	—	45	80	—	100	
Difference of ON resistance between switches	ΔRON	VIN = VILC or VIIC	GND	4.5	—	10	30	—	35	Ω
		Vi/O = VCC to VEE	-4.5	4.5	—	5	12	—	15	
		Ii/O ≤ 2 mA	-6.0	6.0	—	5	10	—	12	
Input/output leakage current (switch off)	I _{OFF}	V _O S = VCC or GND V _I S = GND or VCC V _I N = VILC or VIIC	GND	6.0	—	—	±60	—	±600	nA
Switch input leakage current (switch on, output open)	I _I Z	V _O S = VCC or GND V _I N = VILC or VIIC	GND	6.0	—	—	±60	—	±600	nA
Control input current	I _{IN}	V _I N = VCC or GND	GND	6.0	—	—	±0.1	—	±1.0	μA
Quiescent supply current	I _{CC}	V _I N = VCC or GND	GND	6.0	—	—	4.0	—	40.0	μA
			-6.0	6.0	—	—	8.0	—	80.0	

AC Characteristics (CL = 50 pF, input: tr = tf = 6 ns, GND = 0 V)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
		VEE (V)	VCC (V)	Min	Typ.	Max	Min	Max	
Phase difference between input and output	φI/O	All types	GND	2.0	—	25	60	—	75
			GND	4.5	—	6	12	—	15
			GND	6.0	—	5	10	—	13
			-4.5	4.5	—	4	—	—	—
Output enable time	tpZL tpZH	4051A (Note 1)	GND	2.0	—	64	225	—	280
			GND	4.5	—	18	45	—	56
			GND	6.0	—	15	38	—	48
			-4.5	4.5	—	18	—	—	—
		4052A (Note 1)	GND	2.0	—	64	225	—	280
			GND	4.5	—	18	45	—	56
			GND	6.0	—	15	38	—	48
			-4.5	4.5	—	18	—	—	—
		4053A (Note 1)	GND	2.0	—	50	225	—	280
			GND	4.5	—	14	45	—	56
			GND	6.0	—	12	38	—	48
			-4.5	4.5	—	14	—	—	—
Output disable time	tpLZ tpHZ	4051A (Note 1)	GND	2.0	—	100	250	—	315
			GND	4.5	—	33	50	—	63
			GND	6.0	—	28	43	—	54
			-4.5	4.5	—	29	—	—	—
		4052A (Note 1)	GND	2.0	—	100	250	—	315
			GND	4.5	—	33	50	—	63
			GND	6.0	—	28	43	—	54
			-4.5	4.5	—	29	—	—	—
		4053A (Note 1)	GND	2.0	—	95	225	—	280
			GND	4.5	—	30	45	—	56
			GND	6.0	—	26	38	—	48
			-4.5	4.5	—	26	—	—	—
Control input capacitance	C _{IN}	All types	—	—	—	5	10	—	10 pF
COMMON terminal capacitance	C _{IS}	4051A 4052A 4053A	— -5.0 —	— 5.0 —	— 19 11	36 40 20	70 — —	— 70 40 20	pF
SWITCH terminal capacitance	C _{OS}	4051A 4052A 4053A	— -5.0 —	— 5.0 —	— 7 7	7 15 15	— — —	— 15 15 15	pF
Feedthrough capacitance	C _{IOS}	4051A 4052A 4053A	— -5.0 —	— 5.0 —	— 0.95 0.75	0.95 2 2	— — —	— 2 2 2	pF
Power dissipation capacitance	C _{PD}	4051A (Note 2) 4052A (Note 2) 4053A (Note 2)	GND	5.0	— — —	70 71 67	— — —	— — —	pF

Note 1: RL = 1 kΩ

Note 2: CPD is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$ICC (\text{opr}) = CPD \cdot VCC \cdot f_{IN} + ICC$$

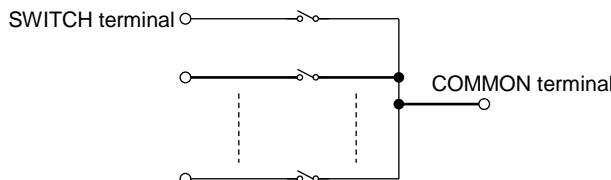
Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note 1)

Characteristics	Symbol	Test Condition	VEE (V)	VCC (V)	Typ.	Unit
Sine wave distortion (T.H.D.)		$R_L = 10 \text{ k}\Omega$, $C_L = 50 \text{ pF}$ $f_{IN} = 1 \text{ kHz}$	$V_{IN} = 4.0 \text{ V}_{\text{p-p}}$	-2.25	2.25	0.025
Frequency response (switch on)	f_{max}	Adjust f_{IN} voltage to obtain 0dBm at V_{OS} Increase f_{IN} frequency until dB meter reads -3dB $R_L = 50 \Omega$, $C_L = 10 \text{ pF}$ $f_{IN} = 1 \text{ MHz}$, sine wave	All (Note 2)	-2.25	2.25	120
			4051A (Note 3)			45
			4052A (Note 3)			70
			4053A (Note 3)			95
			All (Note 2)	-4.5	4.5	190
			4051A (Note 3)			70
			4052A (Note 3)			110
			4053A (Note 3)			150
			All (Note 2)	-6.0	6.0	200
			4051A (Note 3)			85
			4052A (Note 3)			140
			4053A (Note 3)			190
Feed through attenuation (switch off)		V_{IN} is centered at $(V_{CC} - V_{EE})/2$ Adjust input for 0dBm $R_L = 600 \Omega$, $C_L = 50 \text{ pF}$ $f_{IN} = 1 \text{ MHz}$, sine wave	-2.25	2.25	-50	
Crosstalk (control input to signal output)		$R_L = 600 \Omega$, $C_L = 50 \text{ pF}$ $f_{IN} = 1 \text{ MHz}$, square wave ($t_r = t_f = 6 \text{ ns}$)	-4.5	4.5	-50	dB
			-6.0	6.0	-50	
			-2.25	2.25	60	
Crosstalk (between any switches)		Adjust V_{IN} to obtain 0dBm at input $R_L = 600 \Omega$, $C_L = 50 \text{ pF}$ $f_{IN} = 1 \text{ MHz}$, sine wave	-4.5	4.5	140	mV
			-6.0	6.0	200	
			-2.25	2.25	-50	
			-4.5	4.5	-50	dB
			-6.0	6.0	-50	
			-2.25	2.25	-50	

Note 1: These characteristics are determined by design of devices.

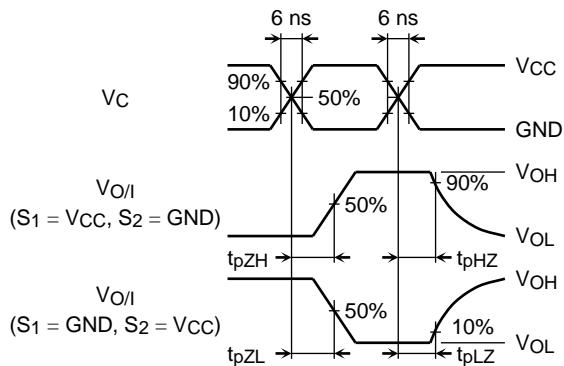
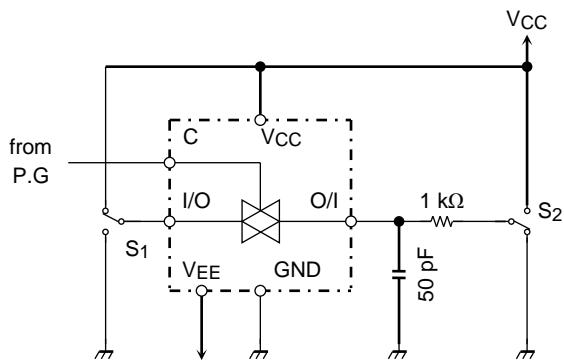
Note 2: Input COMMON terminal, and measured at SWITCH terminal.

Note 3: Input SWITCH terminal, and measured at COMMON terminal.

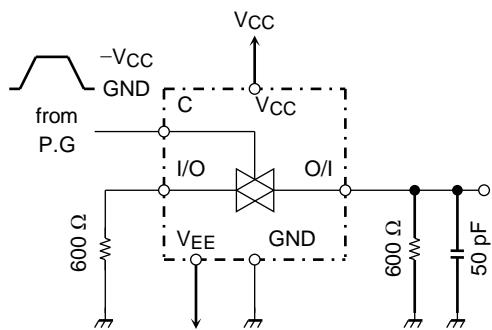


Switching Characteristics Test Circuits

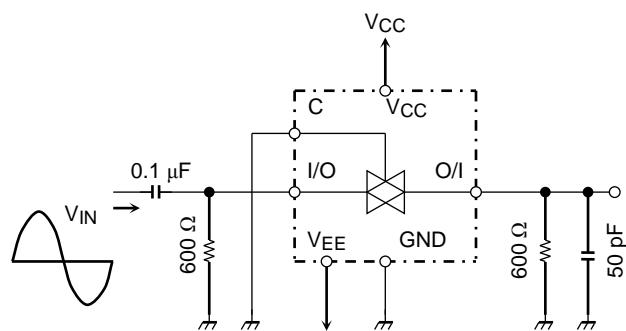
1. tpLZ, tpHZ, tpZL, tpZH



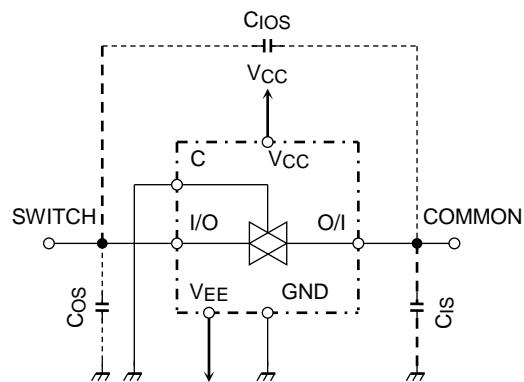
2. Cross Talk (control input-switch output) fIN = 1 MHz duty = 50% tr = tf = 6 ns



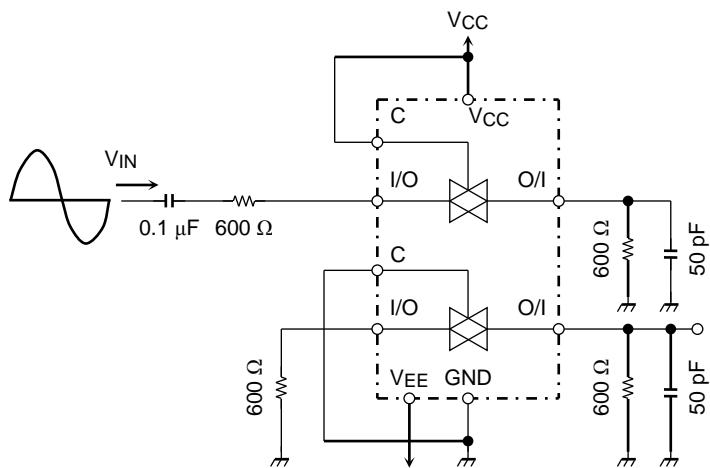
3. Feedthrough Attenuation



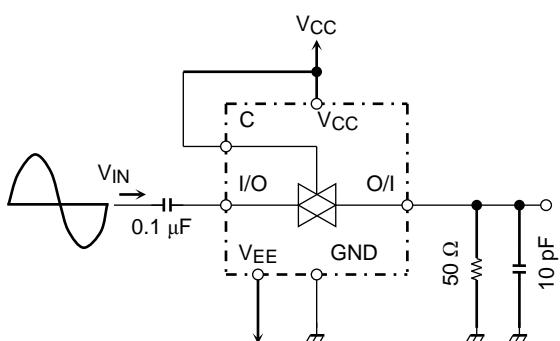
4. Clos, Cis, Cos



5. Cross Talk (between any two switches)



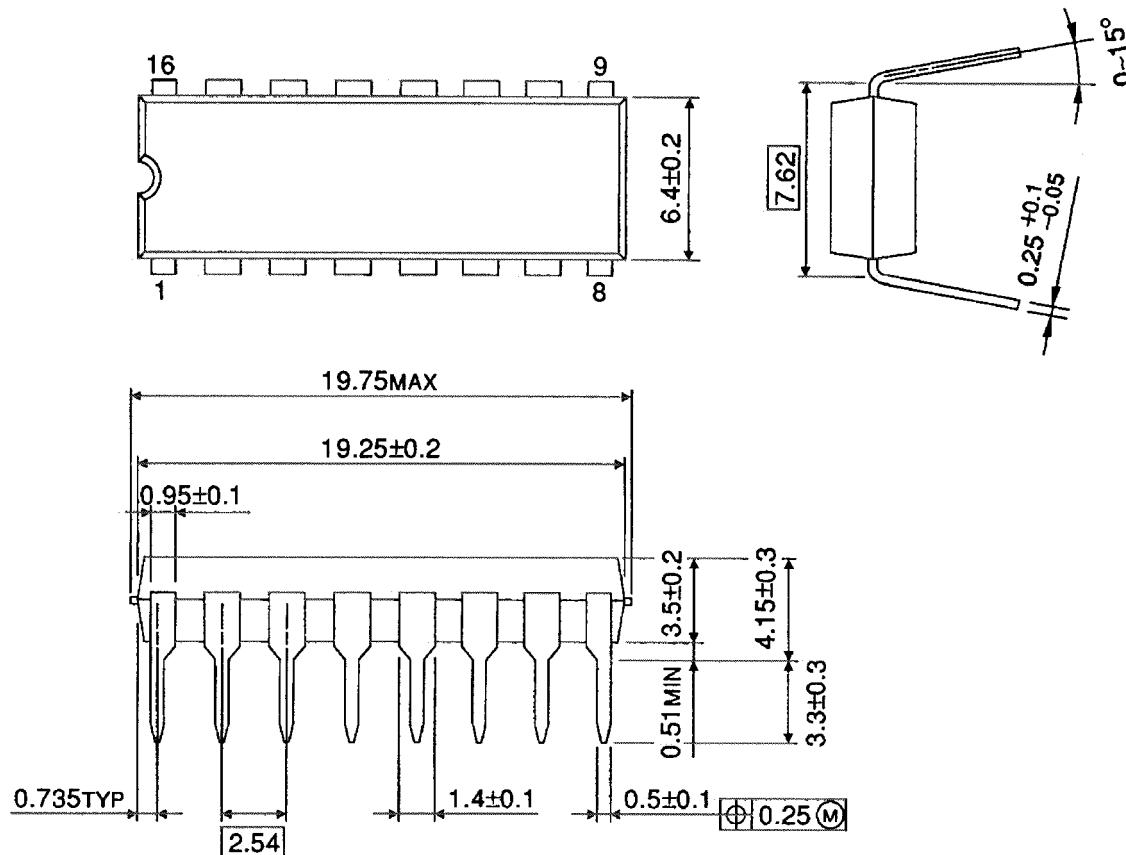
6. Frequency Response (switch on)



Package Dimensions

DIP16-P-300-2.54A

Unit : mm

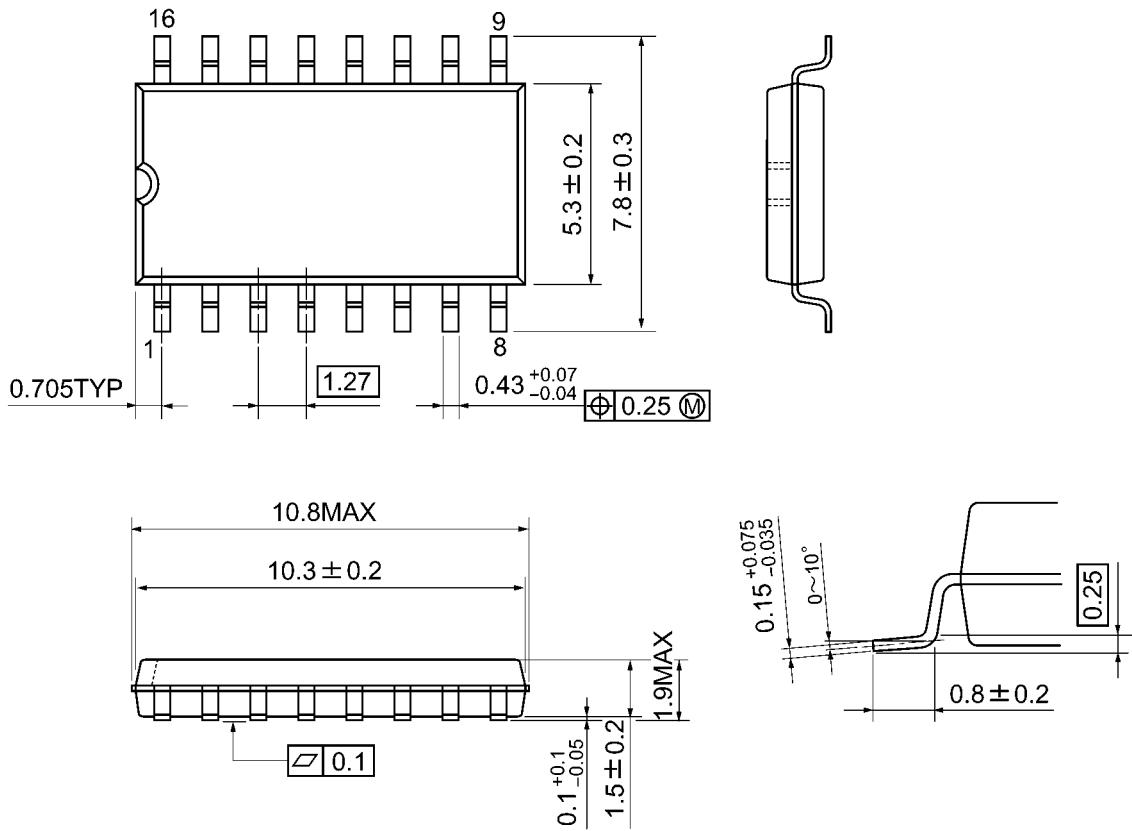


Weight: 1.00 g (typ.)

Package Dimensions

SOP16-P-300-1.27A

Unit: mm

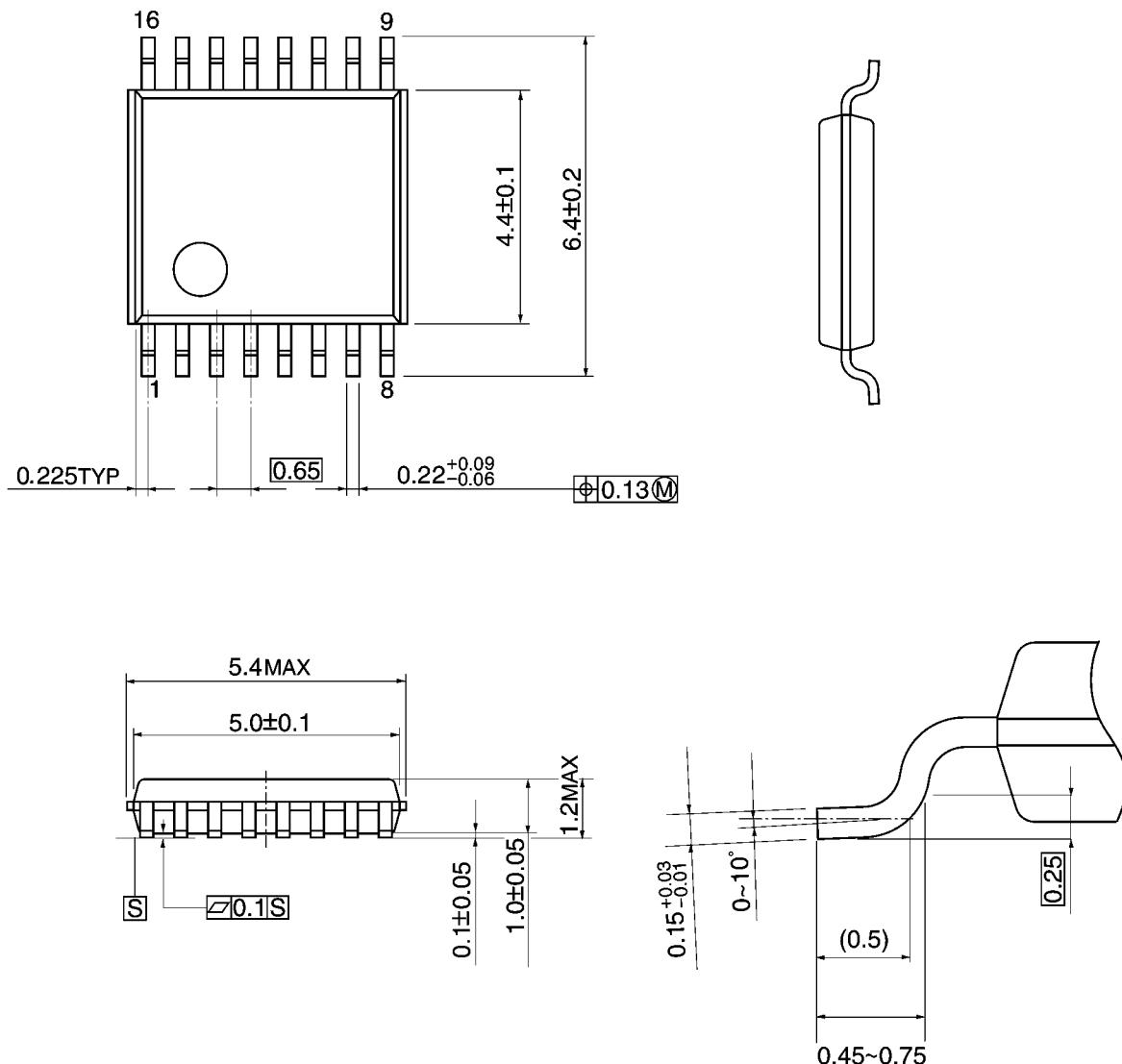


Weight: 0.18 g (typ.)

Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm



Weight: 0.06 g (typ.)